

CLAIMS

What is claimed is:

1. An overlay target comprising:
at least one trench including a series of raised lines.
2. The overlay target of claim 1, wherein said at least one trench comprises a continuous trench defining a geometric shape.
3. The overlay target of claim 1, wherein said at least one trench comprises a plurality of trenches defining said overlay target, each of said plurality of trenches includes a series of raised lines.
4. The overlay target of claim 3, wherein said plurality of trenches includes at least one continuous trench defining a geometric shape.
5. An overlay target comprising:
at least one pad area including a series of raised lines.
6. The overlay target of claim 5, wherein said at least one pad area includes a plurality of pad areas defining said overlay target, each of said plurality of pad areas includes a series of raised lines.
7. The overlay target of claim 6, further comprising at least one trench including a series of raised lines.
8. A semiconductor wafer comprising:
a semiconductor substrate; and
an overlay target comprising at least one series of raised lines.

9. The semiconductor wafer of claim 8, wherein said at least one series of raised lines is etched into said semiconductor substrate.

10. The semiconductor wafer of claim 8, wherein said at least one series of raised lines is etched into a material layer overlying said semiconductor substrate.

11. The semiconductor wafer of claim 8, wherein said at least one series of raised lines is disposed in at least one trench.

12. The semiconductor wafer of claim 11, wherein a plurality of trenches and a corresponding plurality of series of raised lines define said overlay target, each of said plurality of trenches includes one of said plurality of series of raised lines.

13. The semiconductor wafer of claim 8, wherein said at least one series of raised lines is disposed in at least one pad area.

14. The semiconductor wafer of claim 13, wherein a plurality of pad areas and a corresponding plurality of series of raised lines define said overlay target, each of said plurality of pad areas includes one of said plurality of series of raised lines.

15. The semiconductor wafer of claim 8, wherein said at least one series of raised lines comprises a first series of raised lines disposed in a pad area and a second series of raised lines disposed in a trench.